

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal axis direction of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending vertically in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion extending ~~along~~ parallel to said straight portion of said gate electrode, said linear contact portion extending to above said dummy electrode.

2. (Currently Amended) A semiconductor device ~~The semiconductor device of claim 1, comprising:~~

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal direction of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending vertically in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion extending parallel to said straight portion of said gate electrode, said linear contact portion extending to above said dummy electrode;

wherein, in a plan view, each longer side of a rectangle defined by said linear contact portion is located beyond said sidewall insulating film and within a top region of said gate electrode and said dummy electrode, and

a gap between said gate electrode and said dummy electrode is filled with said sidewall insulating film.

3. (Currently Amended) A semiconductor device ~~The semiconductor device of claim 1, comprising:~~

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal direction of said gate electrode;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;
a sidewall insulating film covering a side of said gate electrode, said dummy electrode
and said stopper insulating film;
an interlayer insulating film formed on said semiconductor substrate to cover up said
sidewall insulating film and said stopper insulating film; and
a linear contact portion defined by a conductive member extending vertically in said
interlayer insulating film and electrically connected to one of said source region and said drain
region at its bottom end, said linear contact portion extending parallel to said straight portion of
said gate electrode, said linear contact portion extending to above said dummy electrode;

wherein said gate electrode is arranged in plurality parallel to each other and one of said source region and said drain region constitutes a group of regions of a specified type defined in regions between adjacent two of said gate electrodes being discrete with an isolation insulating film therebetween, and said linear contact portion extends to integrally cover said group of regions of the specified type.

4. (Previously Presented) The semiconductor device of claim 3, wherein said one of said source region and said drain region is electrically connected, via said linear contact portion, to a first interconnection extending, above said linear contact portion, parallel to said straight portion, and the other one of said source region and said drain region is electrically connected to a second interconnection extending, above said gate electrode, transversely to said straight portion of said gate electrode.